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SOT-89

1. BASE







FEATURES

- Low Collector-Emitter Saturation Voltage
- High Breakdown Voltage

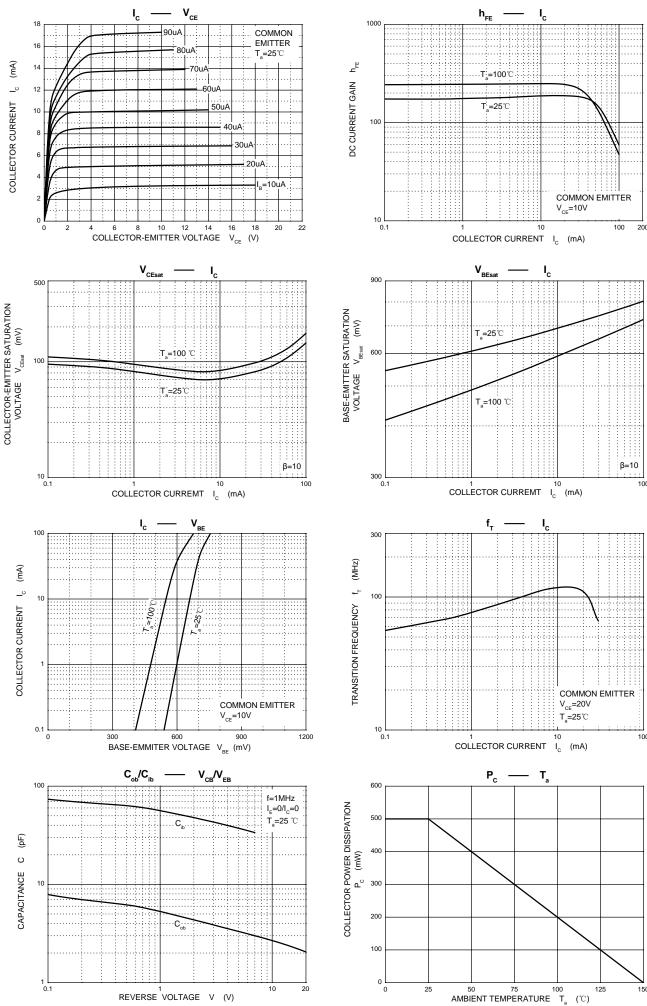
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	310	V
V _{CEO}	Collector-Emitter Voltage	305	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	200	mA
I _{CM}	Collector Current -Pulsed	500	mA
Pc	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a =25°C unless otherwise specified)

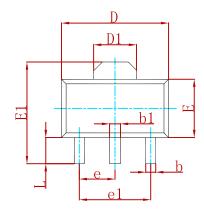
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I _C =100μA,I _E =0	310			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA,I _B =0	305			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I _E =100μA,I _C =0	5			V
	I _{CBO}	V _{CB} =200V,I _E =0			0.25	μΑ
Collector cut-off current	I _{CEX}	V _{CE} =100V,V _X =5V			5	μA
		V _{CE} =300V,V _X =5V			10	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =5V,I _C =0			0.1	μΑ
	h _{FE(1)}	V _{CE} =10V, I _C =1mA	60			
DC current gain	h _{FE(2)}	V _{CE} =10V, I _C =10mA	100		300	
	h _{FE(3)}	V _{CE} =10V, I _C =30mA	75			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =20mA,I _B =2mA			0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =20mA,I _B =2mA			0.9	V
Transition frequency	f⊤	Vce=20V,lc=10mA, f=30MHz	50			MHz

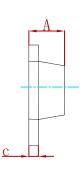
Typical Characteristics



REVERSE VOLTAGE V (V)

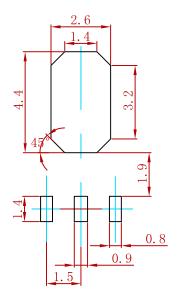
PACKAGE MECHANICAL DATA





Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550 REF.		0.061 REF.		
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000 TYP.		0.118 TYP.		
L	0.900	1.200	0.035	0.047	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
A42	SOT-89	1000



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